

ABSTRACT OF THE DISCLOSURE

An ESD protection circuit comprising a substrate having a first conductivity type, a well region having a second conductivity type, a first doping region having the first conductivity type, and a second doping region having the second conductivity type. The substrate is coupled to the reference potential, the well region is formed on the substrate and electrically coupled to the node, the first doping region is electrically floated on the surface of the well region, and the second doping region is disposed on the substrate and electrically coupled to the reference potential. Moreover, the electrostatic discharge current of the node provides a voltage with sufficient magnitude to breakdown the junction interface between the well region and the substrate, also triggering a BJT comprising the well region, substrate and the second doping region for dissipating the electrostatic discharge current. The first doping region, when its electrostatic discharge current is greater than a predetermined current, reduces the potential difference between the node and the reference potential.